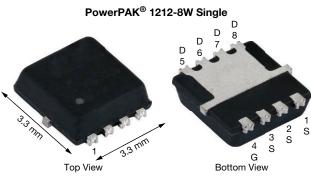
SQ7415CENW

www.vishay.com

Vishay Siliconix

Automotive P-Channel 60 V (D-S) 175 °C MOSFET



Marking code: Q057

PRODUCT SUMMARY					
V _{DS} (V)	-60				
$R_{DS(on)} (\Omega)$ at $V_{GS} = -10 V$	0.065				
$R_{DS(on)} (\Omega)$ at $V_{GS} = -4.5 V$	0.090				
I _D (A)	-16				
Configuration	Single				
Package	PowerPAK 1212-8W				

ABSOLUTE MAXIMUM RATINGS (T _A = 25	°C, unless otherwi	se noted)		
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V _{DS}	-60	v
Gate-source voltage		V _{GS} ± 20	± 20	
Continuous drain current	T _C = 25 °C ª	– I _D	-16	
Continuous drain current	T _C = 125 °C		-11.5	
Continuous source current (diode conduction) ^a		I _S	-16	A
Pulsed drain current ^b		I _{DM}	-64	
Single pulse avalanche current	L = 0.1 mH	I _{AS}	-23	
Single pulse avalanche energy	L = 0.1 MH	E _{AS}	26	mJ
Maximum neuror discinction	T _C = 25 °C	P _D	53	w
Maximum power dissipation	T _C = 125 °C		17	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) ^d			260	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB Mount ^c	R _{thJA}	81	°C/W
Junction-to-case (drain)		R _{thJC}	2.8	C/W

Notes

- a. Package limited
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %
- c. When mounted on 1" square PCB (FR4 material)
- d. See solder profile (<u>www.vishay.com/doc?73257</u>). A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

1

FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

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P-Channel MOSFET





SQ7415CENW



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SPECIFICATIONS ($T_C = 25 \ ^{\circ}C$, $C_C = 25 \ ^{\circ}C$)				NAINI	TVD		
PARAMETER	SYMBOL	IES	MIN.	TYP.	MAX.	UNIT	
Static				[1	1	
Drain-source breakdown voltage	V _{DS}	V _{GS} =	= 0 V, I _D = -250 μA	-60	-	-	v
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	V _{GS} , I _D = -250 μA	-1.5	-2.0	-2.5	
Gate-source leakage	I _{GSS}	V _{DS} =	$=$ 0 V, V _{GS} = \pm 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = -60 V	-	-	-1	
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = -60 V, T _J = 125 °C	-	-	-50	μA
		$V_{GS} = 0 V$	V _{DS} = -60 V, T _J = 175 °C	-	-	-150	
On-state drain current ^a	I _{D(on)}	V _{GS} = -10 V	$V_{DS} \le -5 V$	-15	-	-	Α
		V _{GS} = -10 V	I _D = -5.7 A	-	0.049	0.065	
	R _{DS(on)}	V _{GS} = -10 V	I _D = -5.7 A, T _J = 125 °C	-	-	0.110	_
Drain-source on-state resistance ^a	DO(OII)	V _{GS} = -10 V	I _D = -5.7 A, T _J = 175 °C	-	-	0.136	Ω
		V _{GS} = -4.5 V	I _D = -4.4 A,	-	0.069	0.090	1
Forward transconductance b	g _{fs}		= -15 V, I _D = -5.7 A	-	13	-	S
Dynamic ^b	0.0						
Input capacitance	C _{iss}			-	1083	1385	
Output capacitance	Coss	$V_{GS} = 0 V$	V _{DS} = -25 V, f = 1 MHz	-	132	165	pF
Reverse transfer capacitance	C _{rss}	-		-	80	105	
Total gate charge ^c	Qq			-	25.5	38	
Gate-source charge ^c	Q _{qs}	V _{GS} = -10 V	V _{DS} = -30 V, I _D = -5.7 A	-	4.3	_	nC
Gate-drain charge ^c	Q _{gd}			-	6.4	_	
Gate resistance	⊂gu R _a		f = 1 MHz	3.0	5.6	8.3	Ω
Turn-on delay time ^c	3			-	9	14	
Rise time ^c	t _{d(on)} t _r	-			5	10	
Turn-off delay time c			= -30 V, R _L = 30 Ω V _{GEN} = -10 V, R _g = 1 Ω	_	39	60	ns
Fall time ^c	t _{d(off)}	-	GEN y g	-		12	
	t _f			-	8	12	
Source-drain diode ratings and charact Pulsed current ^a				-		-64	Δ
Forward voltage	I _{SM} V _{SD}		6 A, V _{GS} = 0 V	-	-0.85	-04	A V
Body diode reverse recovery time	vsD t _{rr}			-	26	52	ns
Body diode reverse recovery charge	Q _{rr}	1		-	35	70	nC
Reverse recovery fall time	ta	I _F = -2	A, di/dt = 100A/µs	-	21	-	
Reverse recovery rise time	t _b	1		-	5	-	ns
Body diode peak reverse recovery current	I _{RM(REC)}				-3.2	-	Α

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

b. Guaranteed by design, not subject to production testing

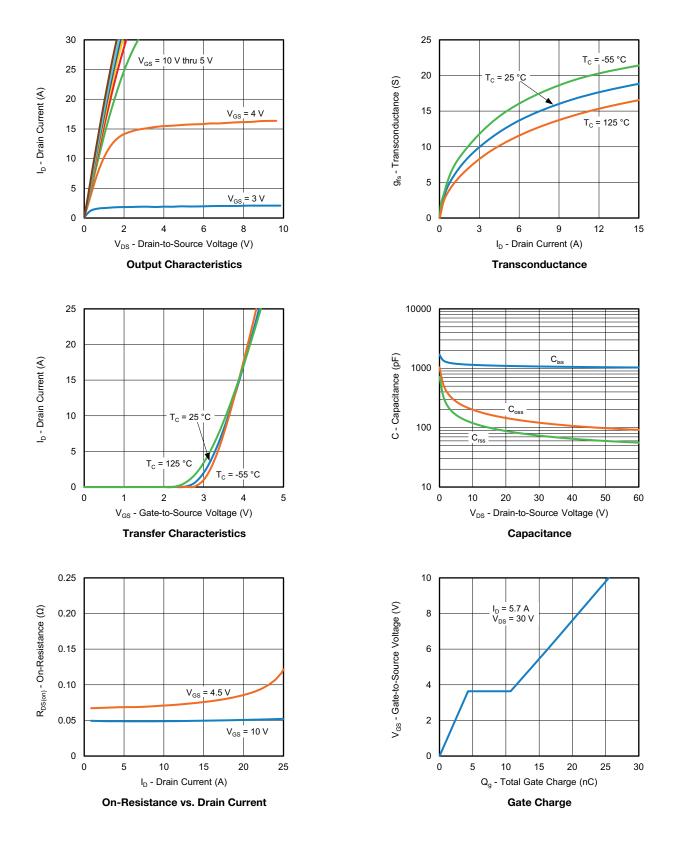
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

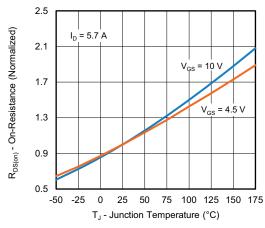


3

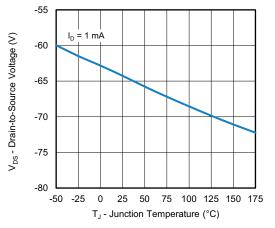
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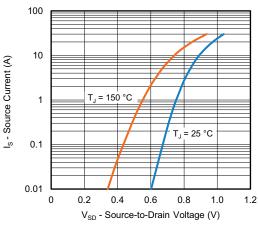
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



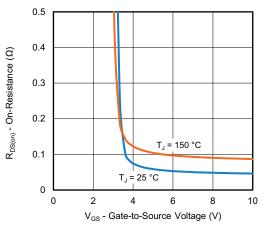
On-Resistance vs. Junction Temperature



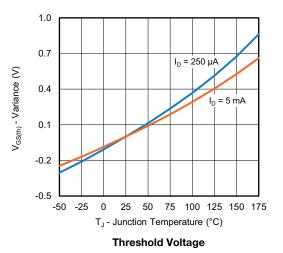
Drain Source Breakdown vs. Junction Temperature

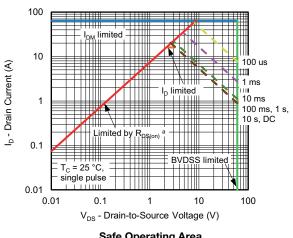


Source Drain Diode Forward Voltage

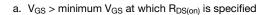


On-Resistance vs. Gate-to-Source Voltage





Safe Operating Area



S22-0760, Rev. C, 05-Sep-2022

4

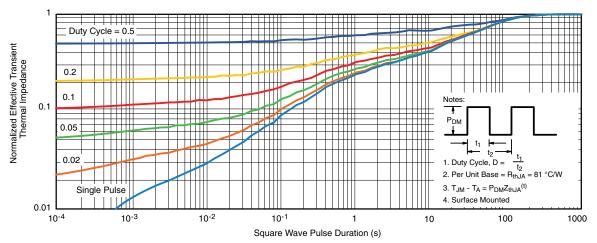
Note

Document Number: 63050

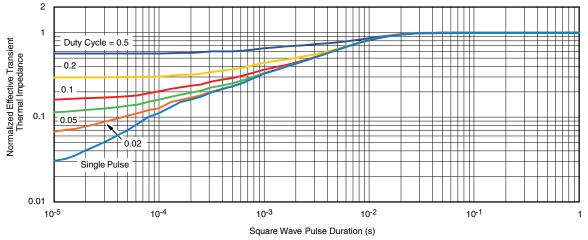
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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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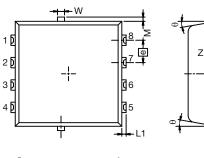
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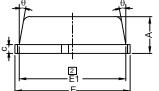


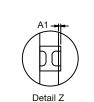
PowerPAK[®] 1212-8W Case Outline

Δ2

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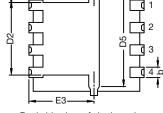




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Б



E2

E4

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Notes
1 Inch will govern

 Dimensions exclusive of mold gate burrs
 Dimensions exclusive of mold flash and cutting burrs

DIM.	MILLIMETERS			INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А	0.97	1.04	1.12	0.038	0.041	0.044	
A1	0	-	0.05	0	-	0.002	
A2	0	-	0.13	0	-	0.005	
b	0.23	0.30	0.41	0.009	0.012	0.016	
С	0.23	0.28	0.33	0.009	0.011	0.013	
D	3.20	3.30	3.40	0.126	0.130	0.134	
D1	2.95	3.05	3.15	0.116	0.120	0.124	
D2	1.98	2.11	2.24	0.078	0.083	0.088	
D4	0.47 typ.				0.0185 typ.		
D5	2.3 typ.				0.090 typ.		
E	3.20	3.30	3.40	0.126	0.130	0.134	
E1	2.95	3.05	3.15	0.116	0.120	0.124	
E2	1.47	1.60	1.73	0.058	0.063	0.068	
E3	1.75	1.85	1.98	0.069	0.073	0.078	
E4		0.34 typ.			0.013 typ.		
е		0.65 BSC.		0.026 BSC			
К		0.86 typ.		0.034 typ.			
Н	0.30	0.41	0.51	0.012	0.016	0.020	
L	0.30	0.43	0.56	0.012	0.017	0.022	
L1	0.06	0.13	0.20	0.002	0.005	0.008	
θ	0°	-	12°	0°	-	12°	
W	0.15	0.25	0.36	0.006	0.010	0.014	
М	0.125 typ.			0.005 typ.			
N: C15-1530-R	ev. B, 16-Nov-15						

Backside view of single pad



RECOMMENDED MINIMUM PADS FOR PowerPAK[®] 1212-8 Single



Recommended Minimum Pads Dimensions in Inches/(mm)

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Revision: 01-Jul-2024